IXYS

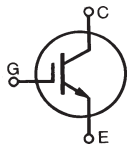
Preliminary Technical Information

GenX3™ 1200V IGBT

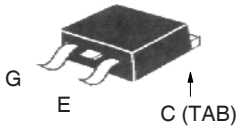
IXGA20N120B3
IXGP20N120B3

V_{CES} = 1200V
I_{C90} = 20A
$V_{CE(sat)}$ ≤ 3.1V

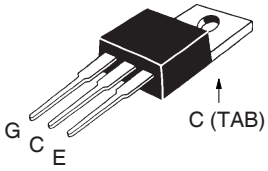
High Speed Low Vsat PT
IGBTs 3-20 kHz Switching



TO-263 (IXGA)



TO-220 (IXGP)



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1200	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	36	A
I_{C90}	T_C = 90°C	20	A
I_{CM}	T_C = 25°C, 1ms	80	A
SSOA (RBSOA)	V_{GE} = 15V, T_J = 125°C, R_G = 15Ω Clamped Inductive load	I_{CM} = 40 @ V_{CE} ≤ 1200	A V
P_C	T_C = 25°C	180	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6mm (0.062 in.) from Case for 10s	260	°C
Weight	TO-263	2.5	g
	TO-220	3.0	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	2.5		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			25	μA
	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 16A, V_{GE} = 15V, Note 2		2.7	3.1	V
	T_J = 125°C		2.8		V

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines
- Inductive Heating

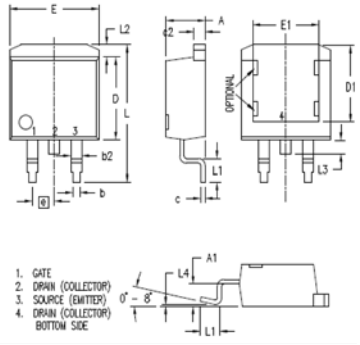
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 16A, V_{CE} = 10V, Note 2	7.5	12.5		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		1070		pF
C_{oes}			80		pF
C_{res}			32		pF
Q_g	I_C = 16A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		51		nC
Q_{ge}			7.4		nC
Q_{gc}			23		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		16		ns
t_{ri}	I_C = 16A, V_{GE} = 15V		31		ns
E_{on}	V_{CE} = 600V, R_G = 15Ω		0.92		mJ
$t_{d(off)}$	Note 1		150		ns
t_{fi}			155		ns
E_{off}			0.56	1.00	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		16		ns
t_{ri}	I_C = 16A, V_{GE} = 15V		45		ns
E_{on}	V_{CE} = 600V, R_G = 15Ω		1.60		mJ
$t_{d(off)}$	Note 1		180		ns
t_{fi}			540		ns
E_{off}			1.63		mJ
R_{thJC}				0.69	°C/W
R_{thCK}	TO-220		0.50		°C/W

Notes:
1. Switching Times may Increase for V_{CE} (Clamp) > 0.5 • V_{CES}, Higher T_J or Increased R_G.
2. Pulse Test, t ≤ 300µs; Duty Cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

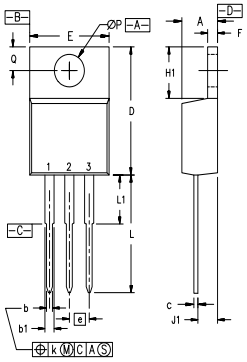
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

TO-263 (IXGA) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXGP) Outline



Pins: 1 - Gate 2 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Fig. 1. Output Characteristics @ 25ºC

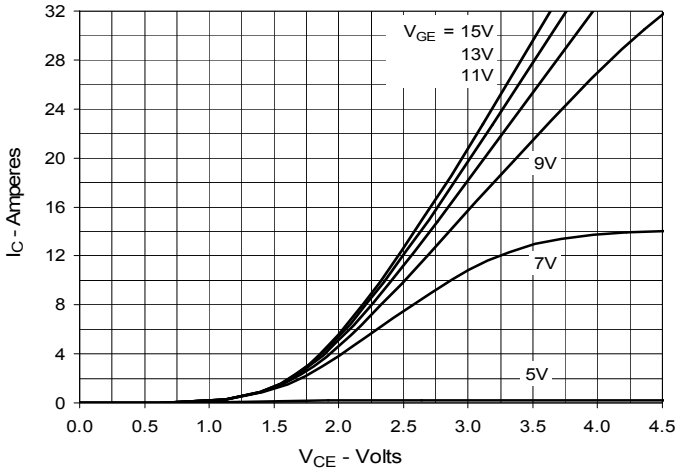


Fig. 2. Extended Output Characteristics @ 25ºC

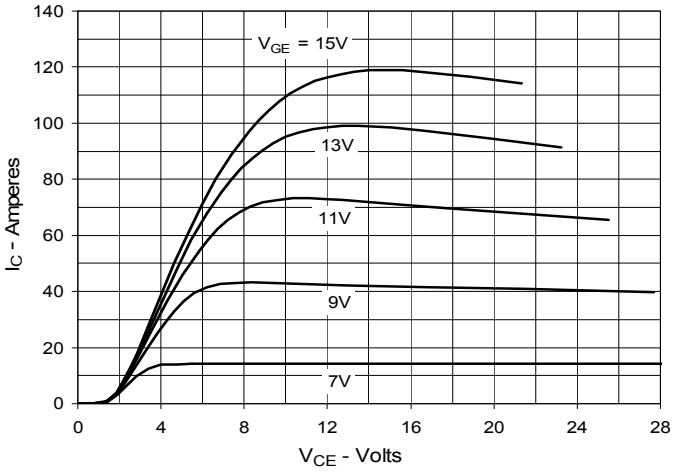


Fig. 3. Output Characteristics @ 125ºC

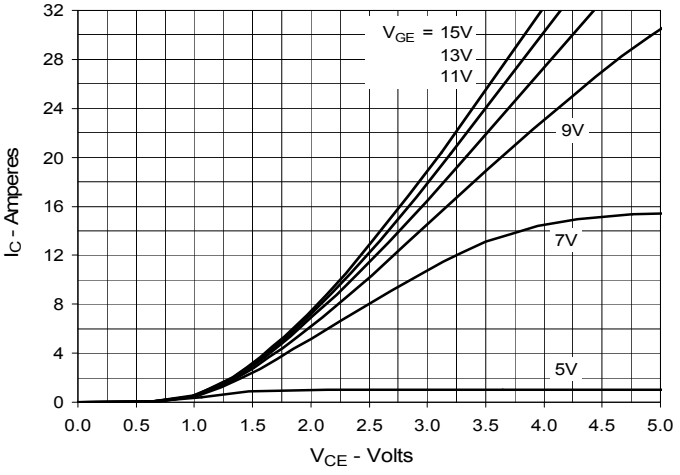


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

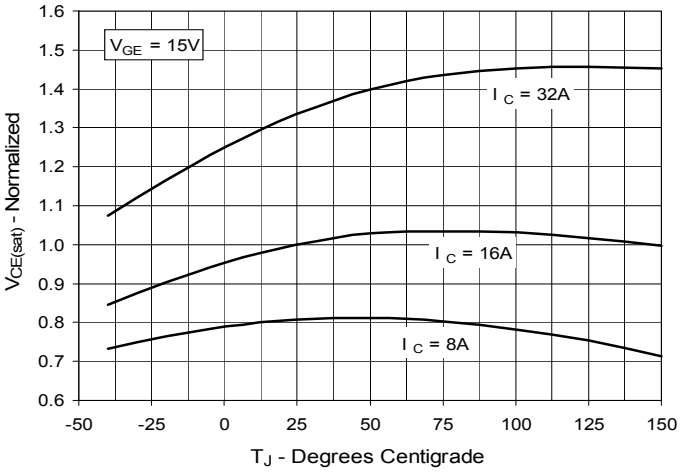


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

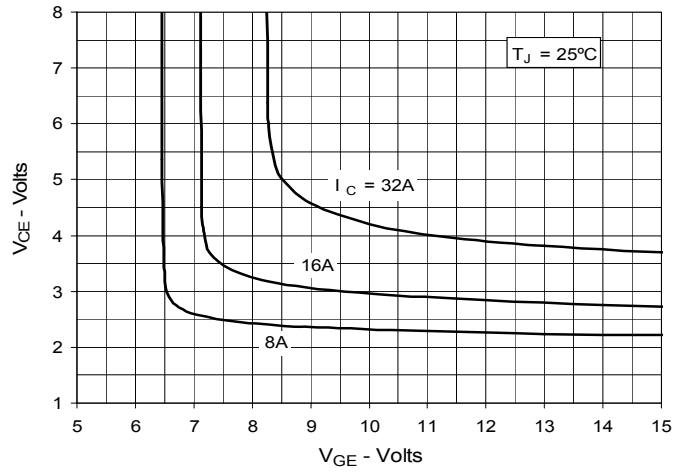


Fig. 6. Input Admittance

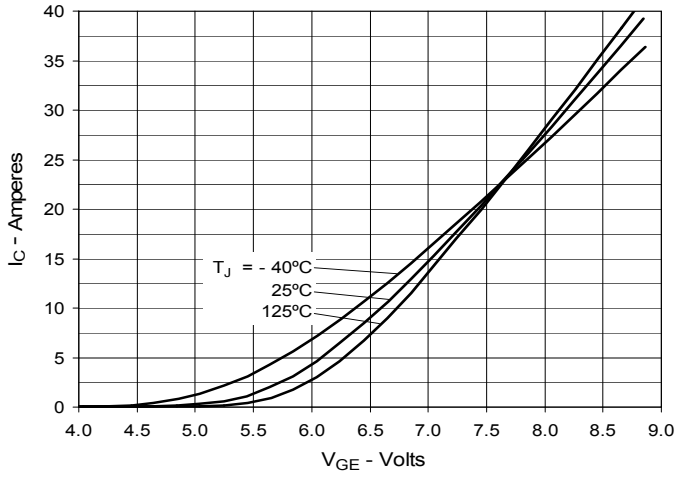


Fig. 7. Transconductance

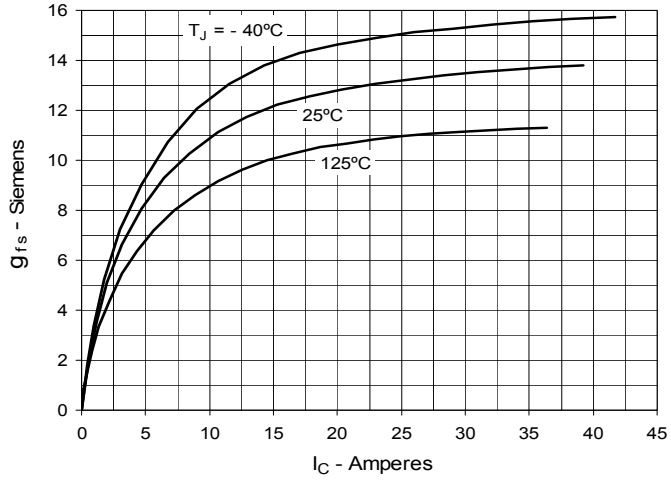


Fig. 8. Gate Charge

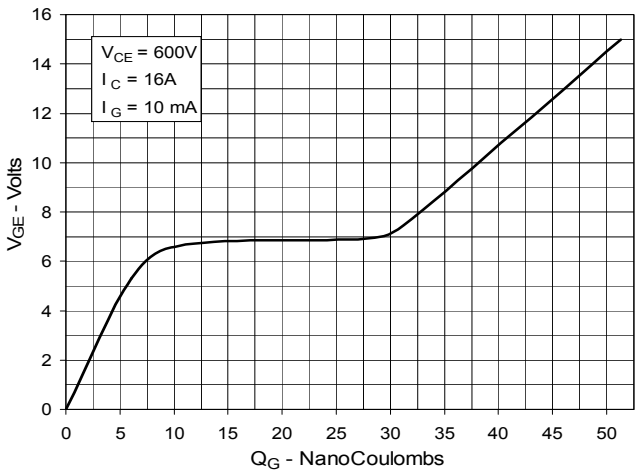


Fig. 9. Capacitance

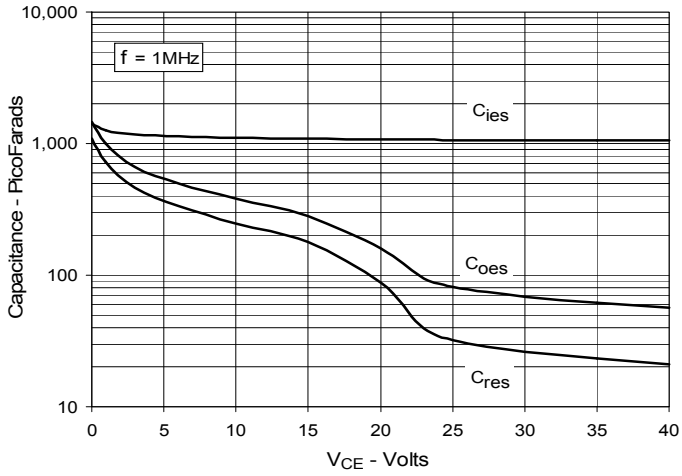


Fig. 10. Reverse-Bias Safe Operating Area

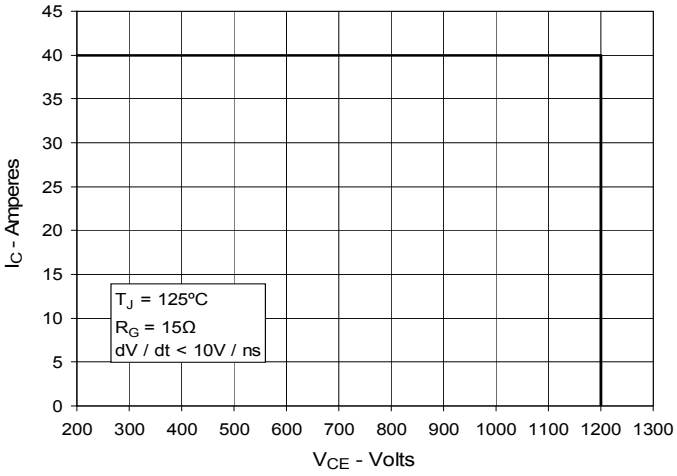


Fig. 11. Maximum Transient Thermal Impedance

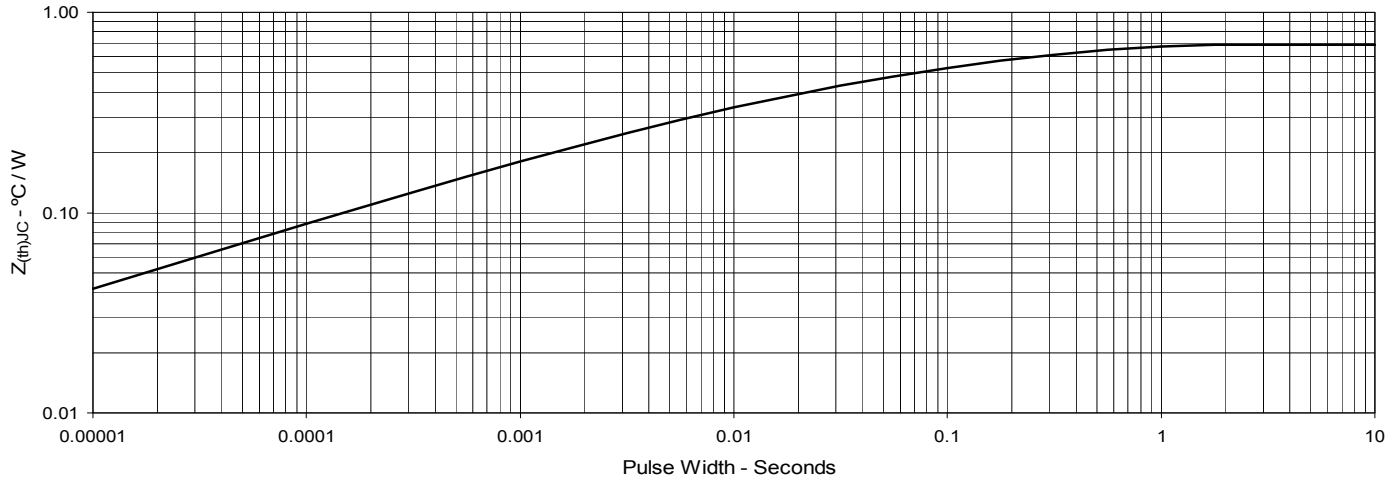


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

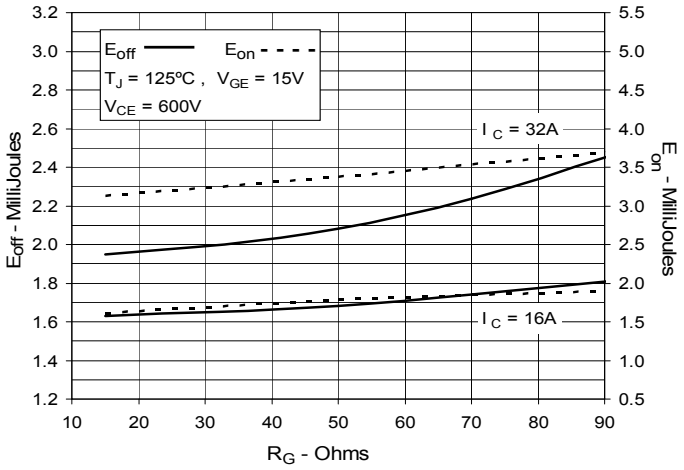


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

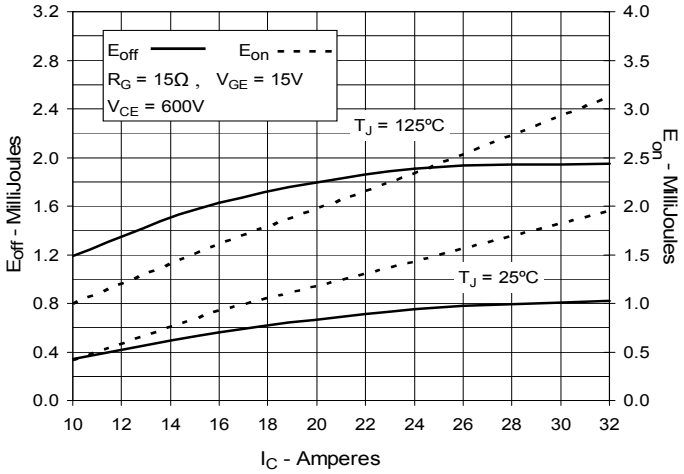


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

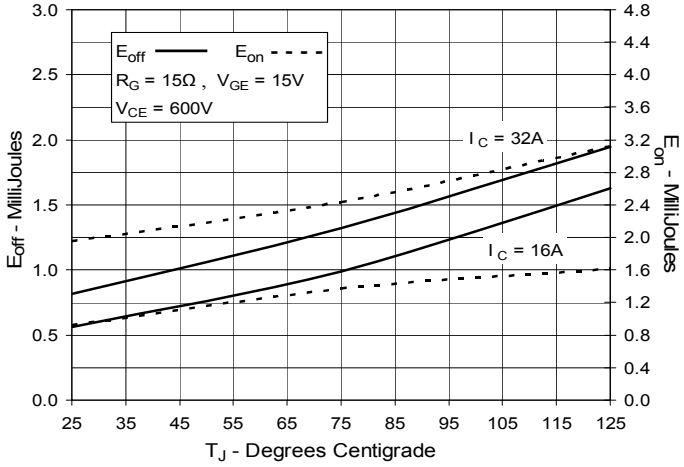


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

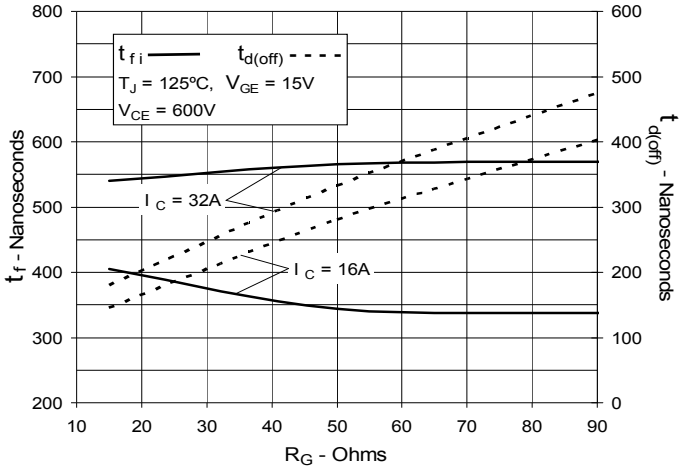


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

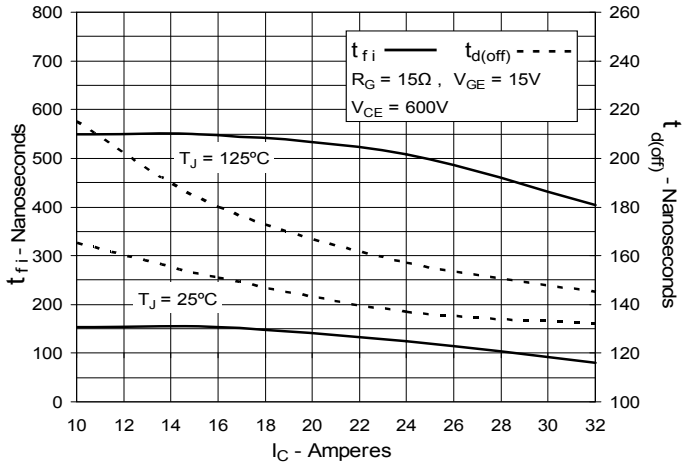


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

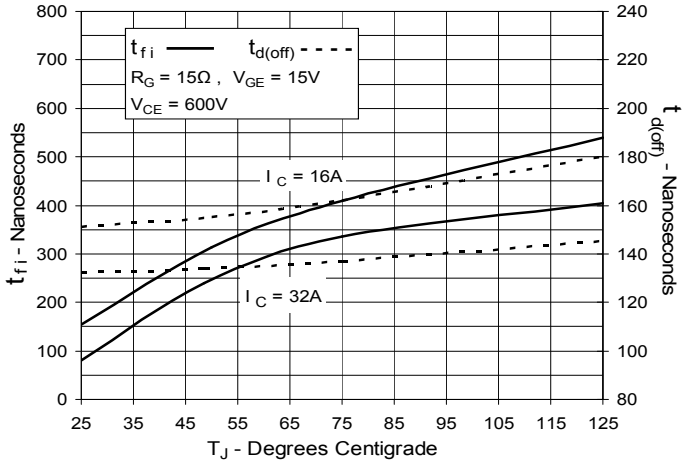


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

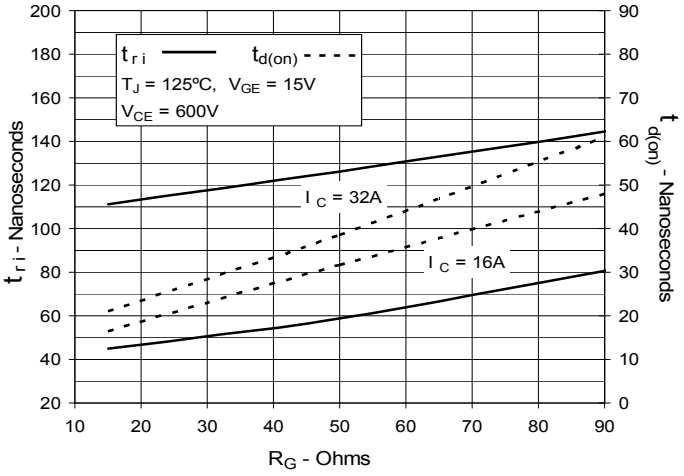


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

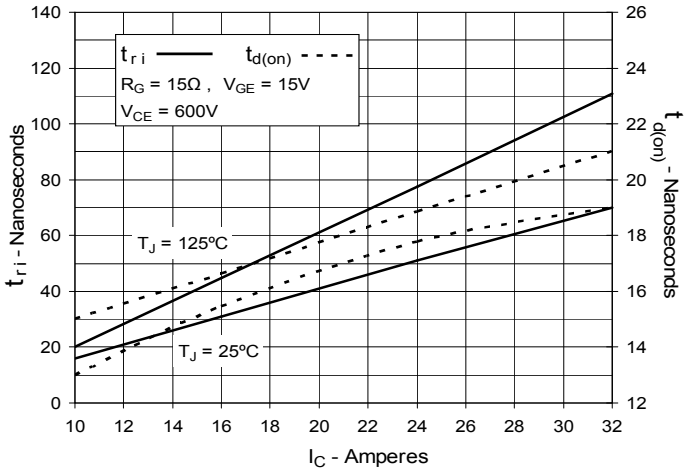


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature